

FEATURES

- 3.45 mm square active area
- Low dark current
- Fast response time
- High speed epitaxy

DESCRIPTION

11.90 mm² High Speed Epitaxy Photodiode with P on N construction. Hermetically packaged in a TO-5 with a clear borosilicate glass window cap.

APPLICATIONS

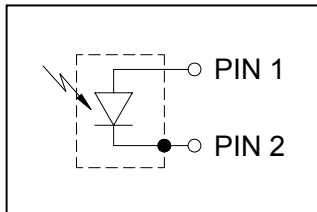
- High speed photometry
- Optical communications
- Pulsed light detection
- Fiber optic light monitoring



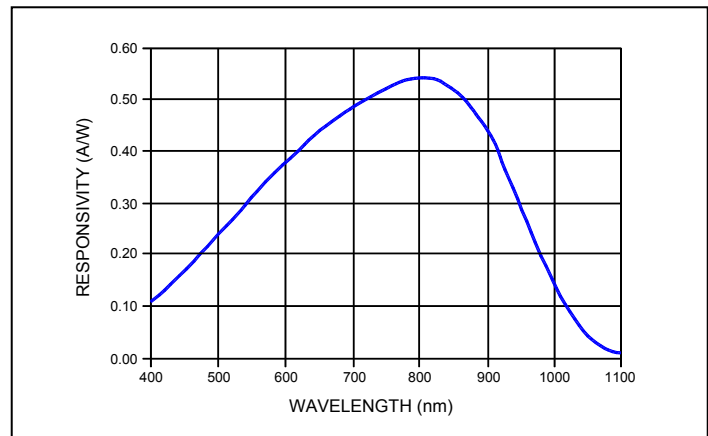
ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	MIN	MAX	UNITS
T _{STG}	Storage Temp	-55	+125	°C
T _{OP}	Operating Temp	-40	+100	°C
V _{R(OP)}	Reverse Operating Voltage	-	50	V
I _{I(PEAK)}	Peak DC Current	-	10	mA

SCHEMATIC



SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS @ 22° C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
R _{SH}	Shunt Resistance	V _R = ±10 mV	100	200	---	MΩ
I _D	Dark Current	V _R = 20 V	---	1.0	3.0	nA
C	Capacitance	V _R = 0 V	---	180	---	pF
		V _R = 20 V	---	40	---	pF
	Responsivity	V _R = 0 V; λ = 632 nm	---	0.40	---	A/W
		V _R = 0 V; λ = 800 nm	---	0.52	---	A/W
NEP	Noise Equivalent Power	V _R = 0 V; λ = 850 nm; R _L = 50 Ω	---	5.0 × 10 ⁻¹⁴	---	W/Hz ^{1/2}
		V _R = 20 V; λ = 850 nm; R _L = 50 Ω	---	1.0 × 10 ⁻¹³	---	W/Hz ^{1/2}
V _{BR}	Breakdown Voltage	I _R = 10 μA	30	50	---	V
t _r	Rise Time	V _R = 20 V; λ = 850 nm; R _L = 50 Ω	---	3.0	---	ns

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

USA:

Pacific Silicon Sensor, Inc.
5700 Corsa Avenue, #105
Westlake Village, CA 91362 USA
Phone (818) 706-3400
Fax (818) 889-7053
Email: sales@pacific-sensor.com
www.pacific-sensor.com

7/9/2009

International sales:

Silicon Sensor International AG
Wilhelminenhofstrasse 76-77
D-12459 Berlin, Germany
Phone +49 (0)30-63 99 23 10
Fax +49 (0)30-63 99 23 33
Email: sales@silicon-sensor.de
www.silicon-sensor.de